



101 028 001

C of

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Ho, Tu-Tu

Patent No.: 7,132,711

Group Art Unit: 2818

Issue Date: November 7, 2006

Docket No: 1303.035US1

**Certificate
of Correction**
DEC 14 2006

Title: PROGRAMMABLE ARRAY LOGIC OR MEMORY WITH P-CHANNEL DEVICES AND
ASYMMETRICAL TUNNEL BARRIERS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
ATTN: CERTIFICATE OF CORRECTION BRANCH

We are transmitting herewith the attached:

- ☒ A check in the amount of \$100.00 to cover the Certificate of Correction fee.
- ☒ Request for Certificate of Correction.
- ☒ Certificate of Correction Form - PTO-1050 (in duplicate)
- ☒ A return postcard.

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer No: 21186

By: Marvin L. Beekman
Name: Marvin L. Beekman
Reg. No. 38,377
MLB:CMG:sj

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria VA 22313-1450, on this 6 day of December 2006.

KATHLEEN E. ROTHROCK
Name

Kathleen E. Rothrock
Signature

DEC 15 2006

Patent 7,132,711

PATENT

IN UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.: 7,132,711

Docket No: 1303.035US1

Issue Date: November 7, 2006

Patentee: Leonard Forbes et al.

Customer No.: 21186

Confirmation No.: 2627

PROGRAMMABLE ARRAY LOGIC OR MEMORY WITH P-CHANNEL
DEVICES AND ASYMMETRICAL TUNNEL BARRIERS

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450
ATTN: CERTIFICATE OF CORRECTION BRANCH

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. Two copies of the text of the Certificate in the suggested form are enclosed.

Pursuant to 1.20(a), enclosed please find a check in the amount of \$100.00.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

The Examiner is authorized to charge any additional fees or credit overpayment to Deposit Account No.19-0743.

Respectfully Submitted

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6900

Date: 12-6-06

By: MLB
Marvin L. Beekman
Reg. No: 38,377
MLB:sj

CERTIFICATE UNDER 37 CFR § 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450, on this 6 day of December 2006

KATHLEEN E. ROTHROCK
Name

Kathleen E Rothrock
Signature

12/12/2006 SLUANG1 00000045 7132711

01 FC:1811

100.00 0P

DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (1) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (73), in "Assignee", in column 1, line 1, after "Inc." insert
-- , 83716 --.

On the face page, in field (57), under "Abstract", in column 2, line 13, delete "metal-oxide"
and insert -- metal oxide --, therefor.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 28, below
"6,163,049 A 12/2000 Bui 257/321" insert -- 6,169,306 1/2001 Gardner et
al. 257/310 --.

On page 2, in field (56), under "Other Publications", in column 2, line 9, delete "Temperture"
and insert -- Temperature --, therefor.

On page 2, in field (56), under "Other Publications", in column 2, line 57, after "Dielectrics
with" delete "Dielectrics with". (Second Occurrence)

On page 3, in field (56), under "Other Publications", in column 1, line 2, delete "Internatonal"
and insert -- International --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 9, delete "Symposium"
and insert -- Symposium --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 9, delete "VSLI" and
insert -- VLSI --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 12, delete "Physics" and
insert -- Physica --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 33, delete "Similiar"
and insert -- Similar --, therefor.

MAILING ADDRESS OF SENDER:

PATENT NO. _____ 7,132,711 _____

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

No. of additional copies



Atty Docket No: 1303.035US1

DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (2) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 3, in field (56), under "Other Publications", in column 2, line 7, delete "propeties" and insert - - properties - -, therefor.

On page 3, in field (56), under "Other Publications", in column 2, line 50, delete "if" and insert - - of - -, therefor.

On Sheet 1 of 17, in FIG. 1C, line 1, delete "VACCUUM" and insert - - VACUUM - -, therefor.

In column 1, line 12, delete "Memory Metal Oxide Tunnel Insulators" and insert - - Floating Gate Memory, Low Tunnel Barrier Interpoly Insulators - -, therefor.

In column 1, line 13, after "09/945,395," insert - - filed August 30, 2001, - -.

In column 1, line 14, after "Insulator," delete ",".

In column 1, line 14, after "09/945,507," insert - - filed August 30, 2001, - -.

In column 1, lines 15-16, delete "Dynamic Electricafly Alterable Programmable Memory with Insulating Metal Oxide Interpoly Insulators" and insert - - Integrated Circuit Memory Device and Method - -, therefor.

In column 1, line 16, delete ""Ser." and insert - - " Ser. - -, therefor.

In column 1, line 17, after "09/945,498," insert - - filed August 30, 2001, - -.

In column 1, line 17, delete "Field" and insert - - In Service - -, therefor.

In column 1, line 18, delete "Metal Oxide and/or" before "Low Tunnel".

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (3) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 1, line 19, after "09/945,512," insert - - filed August 30, 2001, - -.

In column 1, line 20, delete "Metal Oxide Tunnel" and insert - - Low Tunnel Barrier - -, therefor.

In column 1, line 21, after "09/945,554," insert - - filed August 30, 2001, - -.

In column 1, line 22, delete "Devices" and insert - - Circuits - -, therefor.

In column 1, line 23, after "Insulators," insert - - " - -.

In column 1, line 23, after "09/945,500," insert - - filed August 30, 2001, - -.

In column 1, line 55, delete "Nordhiem" and insert - - Nordheim - -, therefor.

In column 2, lines 7-9, delete "FLASH MEMORY WITH MICROCRYSTALLINE SILICON CARBIDE AS THE FLOATING GATE STRUCTURE" and insert - - FLASH MEMORY WITH MICROCRYSTALLINE SILICON CARBIDE FILM FLOATING GATE - -, therefor.

In column 2, lines 14-17, delete "DYNAMIC RANDOM ACCESS MEMORY OPERATION OF A FLASH MEMORY DEVICE WITH CHARGE STORAGE ON A LOW ELECTRON AFFINITY GaN OR GaAlN FLOATING GATE" and insert - - CURSOR CONTROLLING DEVICE AND THE METHOD OF THE SAME - -, therefor.

In column 2, lines 18-21, delete "VARIABLE ELECTRON AFFINITY DIAMOND-LIKE COMPOUNDS FOR GATES IN SILICON CMOS MEMORIES AND IMAGING DEVICES" and insert - - TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. _____ 7,132,711 _____

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (4) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 2, lines 25–27, delete “DRAM CELLS WITH A STRUCTURE SURFACE USING A SELF STRUCTURED MASK” and insert - - METHOD FOR FORMING HIGH CAPACITANCE MEMORY CELLS - -, therefor.

In column 2, lines 29–31, delete “ATOMIC LAYER EXPITAXY GATE INSULATORS AND TEXTURED SURFACES FOR LOW VOLTAGE FLASH MEMORIES” and insert - - ALTERNATE METHOD AND STRUCTURE FOR IMPROVED FLOATING GATE TUNNELING DEVICES - -, therefor.

In column 2, lines 36–38, delete “GATE INSULATOR FOR SILICON INTEGRATED CIRCUIT TECHNOLOGY BY THE CARBURIZATION OF SILICON” and insert - - CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS - -, therefor.

In column 3, line 4, after “Francisco” delete “.” and insert - - , - -, therefor.

In column 3, line 4, after “1984” delete “.” and insert - - ; - -, therefor.

In column 3, line 7, after “Philadelphia” delete “.” and insert - - , - -, therefor.

In column 3, line 10, after “Japan” delete “.” and insert - - , - -, therefor.

In column 3, line 11, after “4,780,424” delete “.” and insert - - , - -, therefor.

In column 3, line 14, after “Spectrum” delete “.” and insert - - , - -, therefor.

In column 3, line 14, after “October” delete “.” and insert - - , - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies

➡

DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (5) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 18, after "5,801,401" delete "." and insert - - , - -, therefor.

In column 3, lines 18 – 19, delete "Flash Memory With Microcrystalline Silicon Carbide As The Floating Gate Structure" and insert - - Flash Memory With Microcrystalline Silicon Carbide Film Floating Gate - -, therefor.

In column 3, line 20, after "5,852,306" delete "." and insert - - , - -, therefor.

In column 3, line 20, delete "Memory" and insert - - Memory - -, therefor.

In column 3, line 22, after "08/908,098" delete "." and insert - - , - -, therefor.

In column 3, lines 22–25, delete "Dynamic Random Access Memory Operation of a Flash Memory Device With Charge Storage On a Low Electron Affinity GaN or GaAlN Floating Gate" and insert - - Cursor Controlling Device and the Method of the Same - -, therefor.

In column 3, line 26, after "08/903452" delete "." and insert - - , - -, therefor.

In column 3, lines 26–28, delete "Variable Electron Affinity Diamond-Like Compounds for Gates in Silicon CMOS Memories and Imaging Devices" and insert - - Transistor With Variable Electron Affinity Gate and Methods of Fabrication and Use - -, therefor.

In column 3, lines 29–30, delete "Drain Cells With A Structure Surface Using A Self Structured Mask" and insert - - Method for Forming High Capacitance Memory Cells - -, therefor.

In column 3, lines 31–33, delete "Atomic Layer Epitaxy Gate Insulators and Textured Surfaces for Low Voltage Flash Memories" and insert - - Alternate Method and Structure for Improved Floating Gate Tunneling Devices - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. _____ 7,132,711 _____

No. of additional copies

➡ _____

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (6) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 34, after "08/903,453" delete "." and insert - - , - -, therefor.

In column 3, lines 34-36, delete "Gate Insulator For Silicon Integrated Circuit Technology by the Carburization of Silicon" and insert - - Carburized Silicon Gate Insulators for Integrated Circuits - -, therefor.

In column 3, line 37, after "09/945,514" delete "." and insert - - , - -, therefor.

In column 3, line 41, after "Insulator" delete "," and insert - - ; - -, therefor.

In column 3, line 42, after "09/780,169" delete "." and insert - - , - -, therefor.

In column 3, line 44, before "Tunneling" insert - - " - -.

In column 3, line 45, delete " Al_2O_1 " and insert - - Al_2O_3 - -, therefor.

In column 3, line 57, delete ""Thin" and insert - - "Thin - -, therefor.

In column 3, line 59, after "Devices" delete "." and insert - - , - -, therefor.

In column 3, line 60, after "Edition" delete "." and insert - - , - -, therefor.

In column 3, line 63, after "Lett." insert - - , - -.

In column 3, line 64, after "Feb." delete ",".

In column 3, line 65, after "Robertson" delete ".".

In column 3, line 67, delete "B." and insert - - B, - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (7) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 4, line 3, after "Lett." insert - - , - -.

In column 4, line 7, delete "B. Vol." and insert - - B, Vol. - -, therefor.

In column 4, line 8, after "3" delete "." and insert - - , - -, therefor.

In column 4, line 19, after "Phys." insert - - , - -.

In column 4, line 20, after "Morris" delete "." and insert - - , - -, therefor.

In column 4, line 22, after "AIME" delete "." and insert - - , - -, therefor.

In column 4, line 25, after "Electronics" delete "." and insert - - , - -, therefor.

In column 4, line 27, after "Soc." insert - - , - -.

In column 4, line 32, delete "Band Gap" and insert - - Bandgap - -, therefor.

In column 4, line 37, after "Luan" delete "." and insert - - , - -, therefor.

In column 4, line 42, delete "Anal." and insert - - Appl. - -, therefor.

In column 4, line 43, after "Lett." insert - - , - -.

In column 4, line 44, after "Guo" delete "." and insert - - , - -, therefor.

In column 4, line 44, delete "Hub" and insert - - High - -, therefor.

MAILING ADDRESS OF SENDER:

PATENT NO. 7,132,711

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

No. of additional copies



Atty Docket No: 1303.035US1

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (8) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 4, lines 45-46, after "Technology" delete "." and insert - - , - -, therefor.

In column 4, line 50, after "Substrates" delete "." and insert - - , - -, therefor.

In column 4, line 52, after "Yan" delete "." and insert - - , - -, therefor.

In column 4, line 52, after "et al." insert - - , - -.

In column 4, line 54, after "Ambient" insert - - , - -.

In column 4, line 54, delete "voL" and insert - - vol. - -, therefor.

In column 4, line 56, delete "Oi." and insert - - Qi, - -, therefor.

In column 4, line 57, after "Si" delete "." and insert - - , - -, therefor.

In column 4, line 58, after "IEDM" delete "." and insert - - , - -, therefor.

In column 4, line 58, after "148" delete ":" and insert - - ; - -, therefor.

In column 4, line 59, delete "Ms." and insert - - Ma, - -, therefor.

In column 4, line 62, after "IEDM" delete "." and insert - - , - -, therefor.

In column 4, line 64, delete "Brrriers" and insert - - Barriers - -, therefor.

In column 4, line 66, after "Lett." insert - - , - -.

In column 4, line 67, after "2001" delete ")".

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. _____ 7,132,711 _____

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (9) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 5, line 2, after "Oxide" delete "." and insert - - , - - , therefor.

In column 5, line 3, after "Soc." insert - - , - - .

In column 5, line 5, delete "Gale" and insert - - Gate - - , therefor.

In column 5, line 6, delete "Y₂O₂" and insert - - Y₂O₃ - - , therefor.

In column 5, line 6, after "Phys." insert - - , - - .

In column 5, line 8, after "09/945,507" delete "." and insert - - , - - , therefor.

In column 5, lines 8-9, delete "Flash Memory Devices With Metal Oxide Interpoly Insulators" and insert - - Flash Memory With Low Tunnel Barrier Interpoly Insulators - - , therefor.

In column 5, line 17, after "1999" delete ")".

In column 5, line 18, delete "patent" and insert - - Patent - - , therefor.

In column 5, line 18, after "09/651,380" delete "." and insert - - , - - , therefor.

In column 5, line 20, after "09/945,507" delete "." and insert - - , - - , therefor.

In column 5, lines 20-21, delete "Flash Memory Devices With Metal Oxide Interpoly Insulators" and insert - - Flash Memory With Low Tunnel Barrier Interpoly Insulators - - , therefor.

In column 5, line 22, after "5,350,738" delete "." and insert - - , - - , therefor.

MAILING ADDRESS OF SENDER:

PATENT NO. 7,132,711

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

No. of additional copies



Atty Docket No: 1303.035US1

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (10) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 5, line 24, after "09/945,137" delete "." and insert - - , - - , therefor.

In column 5, lines 24-25, delete "Low Cost Processes for Producing High Quality Perovskite Dielectric Films" and insert - - Methods of Forming Perovskite-Type Material and Capacitor Dielectric Having Perovskite-Type Crystalline Structure - - , therefor.

In column 7, line 57, delete "nonvolatile" and insert - - non-volatile - - , therefor.

In column 8, line 10, after "PbZrO₃" insert - - . - - .

In column 8, line 39, delete "6,135,175" and insert - - 6,134,175 - - , therefor.

In column 8, line 41, after "transistors," insert - - " - - .

In column 9, line 25, delete "n+wafer" and insert - - n+ wafers - - , therefor.

In column 13, line 22, delete "E₂ ΔV₂/t₂" and insert - - E₂ = ΔV₂/t₂ - - , therefor.

In column 13, line 40, delete "V/23A" and insert - - V/23Å - - , therefor.

In column 13, line 44, delete "(Φ₀)721" and insert - - (Φ₀) 721 - - , therefor.

In column 14, line 28, delete "{111}" and insert - - {111} - - , therefor.

In column 14, line 57, delete "Angstroms" and insert - - Angstroms - - , therefor.

In column 14, line 60, delete "10x" and insert - - 10X - - , therefor.

In column 14, line 64, delete "Mast" and insert - - Most - - , therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (11) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 15, line 63, after "TABLE A" insert - - , - -.

In column 16, line 66, after "bulk" insert - - , - -.

In column 17, line 29, delete "TM(O)TM" and insert - - TM(O)/TM - -, therefor.

In column 17, line 30, after "FIG." delete "2." and insert - - 9. - -, therefor.

In column 17, line 45, delete "(ix)" and insert - - (vi) - -, therefor.

In column 18, line 45, delete "FIG.s" and insert - - FIGS. - -, therefor.

In column 18, lines 61-62, delete "105 to 107" and insert - - 10⁵ to 10⁷ - -, therefor.

In column 18, line 65, after "Al₂O₃" delete ",".

In column 19, line 15, delete "Al₃" and insert - - Al⁺³ - -, therefor.

In column 19, line 39, delete "aluminium" and insert - - aluminum - -, therefor.

In column 19, line 44, after "Angstroms" delete "." and insert - - , - -, therefor.

In column 19, line 52, delete "Conning" and insert - - forming - -, therefor.

In column 19, line 61, after "tunnel" delete ",".

In column 20, line 17, delete "cV." and insert - - eV. - -, therefor.

In column 20, line 30, delete "sonic" and insert - - some - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (12) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 20, line 34, delete "Ta₂O₅" and insert - - Ta₂O₅ - -, therefor.

In column 20, line 43, before "FLASH" insert - - " - -.

In column 20, lines 43-44, delete "FLASH MEMORY DEVICES WITH METAL OXIDE INTERPOLY INSULATORS" and insert - - FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS - -, therefor.

In column 20, line 45, delete "091945,507" and insert - - 09/945,507 - -, therefor.

In column 20, line 53, delete "if" and insert - - rf - -, therefor.

In column 20, line 58, delete "angstroms" and insert - - Angstroms - -, therefor.

In column 21, line 5, after "Capacitors" insert - - , - -.

In column 21, line 24, delete "tool," and insert - - tools - -, therefor.

In column 21, line 35, after "5,000" delete "A" and insert - - Å - -, therefor.

In column 21, line 37, after "having" delete "then" and insert - - their - -, therefor.

In column 21, line 49, after "at high" insert - - temperature. - -.

In column 22, line 29, before "low k" delete "oxide/a" and insert - - oxide/ a - -, therefor.

In column 22, line 29, before "high k" delete "oxide/a" and insert - - oxide/ a - -, therefor.

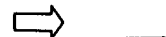
MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (13) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 22, line 46, delete "platinum" and insert - - palladium - -, therefor.

In column 22, line 63, delete "This" and insert - - TMs - -, therefor.

In column 22, line 67, after "Y-Ba-Cu" delete "System" and insert - - system - -, therefor.

In column 24, line 61, after "1114" insert - - , - -.

In column 24, line 62, after "accessing" insert - - . - -.

In column 24, line 64, after "WE*" insert - - , - -.

In column 26, line 15, delete "interploy" and insert - - interpol - -, therefor.

In column 26, line 66, in Claim 8, delete "gale" and insert - - gate - -, therefor.

In column 27, line 55, in Claim 16, delete "funned" and insert - - formed - -, therefor.

In column 27, line 58, in Claim 17, delete "souree" and insert - - source - -, therefor.

In column 27, line 61, in Claim 17, delete "flouting" and insert - - floating - -, therefor.

In column 28, line 11, in Claim 17, delete "funned" and insert - - formed - -, therefor.

In column 28, line 25, in Claim 20, delete "SrTiO₃" and insert - - SrTiO₃ - -, therefor.

In column 28, line 63, in Claim 28, after "transistor" insert - - , - -.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (14) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 29, line 7, in Claim 28, delete "gate." and insert - - gate to promote easier erase operations using electron tunneling from the floating gate to the control gate and to promote longer retention. - -, therefor.

In column 29, line 23, in Claim 29, delete "rentention." and insert - - retention. - -, therefor.

In column 29, line 40, in Claim 34, delete "Perovikite" and insert - - Perovskite - -, therefor.

In column 30, line 38, in Claim 41, delete "operation" and insert - - operations - -, therefor.

In column 30, line 45, in Claim 41, delete "layer" and insert - - layers - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies

➡

DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (1) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (73), in "Assignee", in column 1, line 1, after "Inc." insert
-- , 83716 --.

On the face page, in field (57), under "Abstract", in column 2, line 13, delete "metal-oxide"
and insert -- metal oxide --, therefor.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 28, below
"6,163,049 A 12/2000 Bui 257/321" insert -- 6,169,306 1/2001 Gardner et
al. 257/310 --.

On page 2, in field (56), under "Other Publications", in column 2, line 9, delete "Temperture"
and insert -- Temperature --, therefor.

On page 2, in field (56), under "Other Publications", in column 2, line 57, after "Dielectrics
with" delete "Dielectrics with". (Second Occurrence)

On page 3, in field (56), under "Other Publications", in column 1, line 2, delete "Internatonal"
and insert -- International --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 9, delete "Synposium"
and insert -- Symposium --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 9, delete "VSLI" and
insert -- VLSI --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 12, delete "Physics" and
insert -- Physica --, therefor.

On page 3, in field (56), under "Other Publications", in column 1, line 33, delete "Similiar"
and insert -- Similar --, therefor.

MAILING ADDRESS OF SENDER:

PATENT NO. 7,132,711

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

No. of additional copies



DEC 15 2006

DEC 15 2006

DEC 15 2006

DEC 15 2006

DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (2) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On page 3, in field (56), under "Other Publications", in column 2, line 7, delete "propeties" and insert - - properties - -, therefor.

On page 3, in field (56), under "Other Publications", in column 2, line 50, delete "if" and insert - - of - -, therefor.

On Sheet 1 of 17, in FIG. 1C, line 1, delete "VACCUUM" and insert - - VACUUM - -, therefor.

In column 1, line 12, delete "Memory Metal Oxide Tunnel Insulators" and insert - - Floating Gate Memory, Low Tunnel Barrier Interpoly Insulators - -, therefor.

In column 1, line 13, after "09/945,395," insert - - filed August 30, 2001, - -.

In column 1, line 14, after "Insulator," delete ",".

In column 1, line 14, after "09/945,507," insert - - filed August 30, 2001, - -.

In column 1, lines 15-16, delete "Dynamic Electricafly Alterable Programmable Memory with Insulating Metal Oxide Interpoly Insulators" and insert - - Integrated Circuit Memory Device and Method - -, therefor.

In column 1, line 16, delete ""Ser." and insert - - " Ser. - -, therefor.

In column 1, line 17, after "09/945,498," insert - - filed August 30, 2001, - -.

In column 1, line 17, delete "Field" and insert - - In Service - -, therefor.

In column 1, line 18, delete "Metal Oxide and/or" before "Low Tunnel".

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (3) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 1, line 19, after "09/945,512," insert - - filed August 30, 2001, - -.

In column 1, line 20, delete "Metal Oxide Tunnel" and insert - - Low Tunnel Barrier - -, therefor.

In column 1, line 21, after "09/945,554," insert - - filed August 30, 2001, - -.

In column 1, line 22, delete "Devices" and insert - - Circuits - -, therefor.

In column 1, line 23, after "Insulators," insert - - - -.

In column 1, line 23, after "09/945,500," insert - - filed August 30, 2001, - -.

In column 1, line 55, delete "Nordhiem" and insert - - Nordheim - -, therefor.

In column 2, lines 7-9, delete "FLASH MEMORY WITH MICROCRYSTALLINE SILICON CARBIDE AS THE FLOATING GATE STRUCTURE" and insert - - FLASH MEMORY WITH MICROCRYSTALLINE SILICON CARBIDE FILM FLOATING GATE - -, therefor.

In column 2, lines 14-17, delete "DYNAMIC RANDOM ACCESS MEMORY OPERATION OF A FLASH MEMORY DEVICE WITH CHARGE STORAGE ON A LOW ELECTRON AFFINITY GaN OR GaAlN FLOATING GATE" and insert - - CURSOR CONTROLLING DEVICE AND THE METHOD OF THE SAME - -, therefor.

In column 2, lines 18-21, delete "VARIABLE ELECTRON AFFINITY DIAMOND-LIKE COMPOUNDS FOR GATES IN SILICON CMOS MEMORIES AND IMAGING DEVICES" and insert - - TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies

DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (4) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 2, lines 25–27, delete “DRAM CELLS WITH A STRUCTURE SURFACE USING A SELF STRUCTURED MASK” and insert - - METHOD FOR FORMING HIGH CAPACITANCE MEMORY CELLS - -, therefor.

In column 2, lines 29–31, delete “ATOMIC LAYER EXPITAXY GATE INSULATORS AND TEXTURED SURFACES FOR LOW VOLTAGE FLASH MEMORIES” and insert - - ALTERNATE METHOD AND STRUCTURE FOR IMPROVED FLOATING GATE TUNNELING DEVICES - -, therefor.

In column 2, lines 36–38, delete “GATE INSULATOR FOR SILICON INTEGRATED CIRCUIT TECHNOLOGY BY THE CARBURIZATION OF SILICON” and insert - - CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS - -, therefor.

In column 3, line 4, after “Francisco” delete “.” and insert - - , - -, therefor.

In column 3, line 4, after “1984” delete “.” and insert - - ; - -, therefor.

In column 3, line 7, after “Philadelphia” delete “.” and insert - - , - -, therefor.

In column 3, line 10, after “Japan” delete “.” and insert - - , - -, therefor.

In column 3, line 11, after “4,780,424” delete “.” and insert - - , - -, therefor.

In column 3, line 14, after “Spectrum” delete “.” and insert - - , - -, therefor.

In column 3, line 14, after “October” delete “.” and insert - - , - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (5) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 18, after "5,801,401" delete "." and insert - - , - -, therefor.

In column 3, lines 18 – 19, delete "Flash Memory With Microcrystalline Silicon Carbide As The Floating Gate Structure" and insert - - Flash Memory With Microcrystalline Silicon Carbide Film Floating Gate - -, therefor.

In column 3, line 20, after "5,852,306" delete "." and insert - - , - -, therefor.

In column 3, line 20, delete "MemorY" and insert - - Memory - -, therefor.

In column 3, line 22, after "08/908,098" delete "." and insert - - , - -, therefor.

In column 3, lines 22–25, delete "Dynamic Random Access Memory Operation of a Flash Memory Device With Charge Storage On a Low Electron Affinity GaN or GaAlN Floating Gate" and insert - - Cursor Controlling Device and the Method of the Same - -, therefor.

In column 3, line 26, after "08/903452" delete "." and insert - - , - -, therefor.

In column 3, lines 26–28, delete "Variable Electron Affinity Diamond-Like Compounds for Gates in Silicon CMOS Memories and Imaging Devices" and insert - - Transistor With Variable Electron Affinity Gate and Methods of Fabrication and Use - -, therefor.

In column 3, lines 29–30, delete "Drain Cells With A Structure Surface Using A Self Structured Mask" and insert - - Method for Forming High Capacitance Memory Cells - -, therefor.

In column 3, lines 31–33, delete "Atomic Layer Epitaxy Gate Insulators and Textured Surfaces for Low Voltage Flash Memories" and insert - - Alternate Method and Structure for Improved Floating Gate Tunneling Devices - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (6) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 34, after "08/903,453" delete "." and insert - - , - - , therefor.

In column 3, lines 34-36, delete "Gate Insulator For Silicon Integrated Circuit Technology by the Carburization of Silicon" and insert - - Carburized Silicon Gate Insulators for Integrated Circuits - - , therefor.

In column 3, line 37, after "09/945,514" delete "." and insert - - , - - , therefor.

In column 3, line 41, after "Insulator" delete "," and insert - - ; - - , therefor.

In column 3, line 42, after "09/780,169" delete "." and insert - - , - - , therefor.

In column 3, line 44, before "Tunneling" insert - - " - - .

In column 3, line 45, delete " Al_2O_1 " and insert - - Al_2O_3 - - , therefor.

In column 3, line 57, delete ""Thin" and insert - - " Thin - - , therefor.

In column 3, line 59, after "Devices" delete "." and insert - - , - - , therefor.

In column 3, line 60, after "Edition" delete "." and insert - - , - - , therefor.

In column 3, line 63, after "Lett." insert - - , - - .

In column 3, line 64, after "Feb." delete ",".

In column 3, line 65, after "Robertson" delete ".".

In column 3, line 67, delete "B." and insert - - B, - - , therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (7) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 4, line 3, after "Lett." insert - - , - -.

In column 4, line 7, delete "B. VoL" and insert - - B, Vol. - -, therefor.

In column 4, line 8, after "3" delete "." and insert - - , - -, therefor.

In column 4, line 19, after "Phys." insert - - , - -.

In column 4, line 20, after "Morris" delete "." and insert - - , - -, therefor.

In column 4, line 22, after "AIME" delete "." and insert - - , - -, therefor.

In column 4, line 25, after "Electronics" delete "." and insert - - , - -, therefor.

In column 4, line 27, after "Soc." insert - - , - -.

In column 4, line 32, delete "Band Gap" and insert - - Bandgap - -, therefor.

In column 4, line 37, after "Luan" delete "." and insert - - , - -, therefor.

In column 4, line 42, delete "Anal." and insert - - Appl. - -, therefor.

In column 4, line 43, after "Lett." insert - - , - -.

In column 4, line 44, after "Guo" delete "." and insert - - , - -, therefor.

In column 4, line 44, delete "Hub" and insert - - High - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (8) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 4, lines 45-46, after "Technology" delete "." and insert - - , - - , therefor.

In column 4, line 50, after "Substrates" delete "." and insert - - , - - , therefor.

In column 4, line 52, after "Yan" delete "." and insert - - , - - , therefor.

In column 4, line 52, after "et al." insert - - , - - .

In column 4, line 54, after "Ambient" insert - - , - - .

In column 4, line 54, delete "vol" and insert - - vol. - - , therefor.

In column 4, line 56, delete "Oi." and insert - - Qi, - - , therefor.

In column 4, line 57, after "Si" delete "." and insert - - , - - , therefor.

In column 4, line 58, after "IEDM" delete "." and insert - - , - - , therefor.

In column 4, line 58, after "148" delete ":" and insert - - ; - - , therefor.

In column 4, line 59, delete "Ms." and insert - - Ma, - - , therefor.

In column 4, line 62, after "IEDM" delete "." and insert - - , - - , therefor.

In column 4, line 64, delete "Briers" and insert - - Barriers - - , therefor.

In column 4, line 66, after "Lett." insert - - , - - .

In column 4, line 67, after "2001" delete ")".

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (9) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 5, line 2, after "Oxide" delete "." and insert - - , - - , therefor.

In column 5, line 3, after "Soc." insert - - , - - .

In column 5, line 5, delete "Gale" and insert - - Gate - - , therefor.

In column 5, line 6, delete "Y₂O₂" and insert - - Y₂O₃ - - , therefor.

In column 5, line 6, after "Phys." insert - - , - - .

In column 5, line 8, after "09/945,507" delete "." and insert - - , - - , therefor.

In column 5, lines 8-9, delete "Flash Memory Devices With Metal Oxide Interpoly Insulators" and insert - - Flash Memory With Low Tunnel Barrier Interpoly Insulators - - , therefor.

In column 5, line 17, after "1999" delete ")".

In column 5, line 18, delete "patent" and insert - - Patent - - , therefor.

In column 5, line 18, after "09/651,380" delete "." and insert - - , - - , therefor.

In column 5, line 20, after "09/945,507" delete "." and insert - - , - - , therefor.

In column 5, lines 20-21, delete "Flash Memory Devices With Metal Oxide Interpoly Insulators" and insert - - Flash Memory With Low Tunnel Barrier Interpoly Insulators - - , therefor.

In column 5, line 22, after "5,350,738" delete "." and insert - - , - - , therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (10) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 5, line 24, after "09/945,137" delete "." and insert - - , - -, therefor.

In column 5, lines 24-25, delete "Low Cost Processes for Producing High Quality Perovskite Dielectric Films" and insert - - Methods of Forming Perovskite-Type Material and Capacitor Dielectric Having Perovskite-Type Crystalline Structure - -, therefor.

In column 7, line 57, delete "nonvolatile" and insert - - non-volatile - -, therefor.

In column 8, line 10, after "PbZrO₃" insert - - . - -.

In column 8, line 39, delete "6,135,175" and insert - - 6,134,175 - -, therefor.

In column 8, line 41, after "transistors," insert - - " - -.

In column 9, line 25, delete "n+wafer" and insert - - n+ wafers - -, therefor.

In column 13, line 22, delete "E² ΔV²/t²" and insert - - E² = ΔV²/t² - -, therefor.

In column 13, line 40, delete "V/23A" and insert - - V/23Å - -, therefor.

In column 13, line 44, delete "(Φ₀)721" and insert - - (Φ₀) 721 - -, therefor.

In column 14, line 28, delete "(111)" and insert - - {111} - -, therefor.

In column 14, line 57, delete "Angstroms" and insert - - Angstroms - -, therefor.

In column 14, line 60, delete "10x" and insert - - 10X - -, therefor.

In column 14, line 64, delete "Mast" and insert - - Most - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : 7,132,711

Page (11) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 15, line 63, after "TABLE A" insert - - , - -.

In column 16, line 66, after "bulk" insert - - , - -.

In column 17, line 29, delete "TM(O)TM" and insert - - TM(O)/TM - -, therefor.

In column 17, line 30, after "FIG." delete "2." and insert - - 9. - -, therefor.

In column 17, line 45, delete "(ix)" and insert - - (vi) - -, therefor.

In column 18, line 45, delete "FIG.s" and insert - - FIGS. - -, therefor.

In column 18, lines 61-62, delete "105 to 107" and insert - - 10⁵ to 10⁷ - -, therefor.

In column 18, line 65, after "Al₂O₃" delete ",".

In column 19, line 15, delete "Al₃" and insert - - Al⁺³ - -, therefor.

In column 19, line 39, delete "aluminium" and insert - - aluminum - -, therefor.

In column 19, line 44, after "Angstroms" delete "." and insert - - , - -, therefor.

In column 19, line 52, delete "Conning" and insert - - forming - -, therefor.

In column 19, line 61, after "tunnel" delete ",".

In column 20, line 17, delete "cV." and insert - - eV. - -, therefor.

In column 20, line 30, delete "sonic" and insert - - some - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (12) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 20, line 34, delete "Ta₂O₅" and insert - - Ta₂O₅ - -, therefor.

In column 20, line 43, before "FLASH" insert - - " - -.

In column 20, lines 43-44, delete "FLASH MEMORY DEVICES WITH METAL OXIDE INTERPOLY INSULATORS" and insert - - FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS - -, therefor.

In column 20, line 45, delete "091945,507" and insert - - 09/945,507 - -, therefor.

In column 20, line 53, delete "if" and insert - - rf - -, therefor.

In column 20, line 58, delete "angstroms" and insert - - Angstroms - -, therefor.

In column 21, line 5, after "Capacitors" insert - - , - -.

In column 21, line 24, delete "tool;" and insert - - tools - -, therefor.

In column 21, line 35, after "5,000" delete "A" and insert - - Å - -, therefor.

In column 21, line 37, after "having" delete "then" and insert - - their - -, therefor.

In column 21, line 49, after "at high" insert - - temperature. - -.

In column 22, line 29, before "low k" delete "oxide/a" and insert - - oxide/ a - -, therefor.

In column 22, line 29, before "high k" delete "oxide/a" and insert - - oxide/ a - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (13) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 22, line 46, delete "platinum" and insert - - palladium - -, therefor.

In column 22, line 63, delete "This" and insert - - TMs - -, therefor.

In column 22, line 67, after "Y-Ba-Cu" delete "System" and insert - - system - -, therefor.

In column 24, line 61, after "1114" insert - - , - -.

In column 24, line 62, after "accessing" insert - - . - -.

In column 24, line 64, after "WE*" insert - - , - -.

In column 26, line 15, delete "interplay" and insert - - interpoly - -, therefor.

In column 26, line 66, in Claim 8, delete "gale" and insert - - gate - -, therefor.

In column 27, line 55, in Claim 16, delete "funned" and insert - - formed - -, therefor.

In column 27, line 58, in Claim 17, delete "souree" and insert - - source - -, therefor.

In column 27, line 61, in Claim 17, delete "flouting" and insert - - floating - -, therefor.

In column 28, line 11, in Claim 17, delete "funned" and insert - - formed - -, therefor.

In column 28, line 25, in Claim 20, delete "SrTiO₃" and insert - - SrTiO₃ - -, therefor.

In column 28, line 63, in Claim 28, after "transistor" insert - - , - -.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.
(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 7,132,711

Page (14) of 14

DATED : November 7, 2006

INVENTOR(S) : Forbes et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 29, line 7, in Claim 28, delete "gate." and insert - - gate to promote easier erase operations using electron tunneling from the floating gate to the control gate and to promote longer retention. - -, therefor.

In column 29, line 23, in Claim 29, delete "rentention." and insert - - retention. - -, therefor.

In column 29, line 40, in Claim 34, delete "Perovikite" and insert - - Perovskite - -, therefor.

In column 30, line 38, in Claim 41, delete "operation" and insert - - operations - -, therefor.

In column 30, line 45, in Claim 41, delete "layer" and insert - - layers - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.
P.O. BOX 2938
Minneapolis, MN 55402

Atty Docket No: 1303.035US1

PATENT NO. 7,132,711

No. of additional copies



DEC 15 2006